



#### 60V SOT223 N-channel enhancement mode MOSFET

#### **Product Summary**

BV <sub>DSS</sub>	R <sub>DS(on) max</sub>	I <sub>D</sub> T <sub>A</sub> = +25°C
60V	50mΩ @ V <sub>GS</sub> = 10V	6.7A
00 V	$70 \text{m}\Omega$ @ $V_{GS} = 4.5V$	5.7A

#### **Description**

This new generation MOSFET is designed to minimize the on-state resistance (R<sub>DS(ON)</sub>) and yet maintain superior switching performance, making it ideal for high-efficiency power management applications.

### **Applications**

- DC-DC Converters
- Power Management Functions
- Backlighting

#### **Features and Benefits**

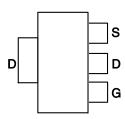
- Low Input Capacitance
- Low On-Resistance
- · Fast Switching Speed
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

#### **Mechanical Data**

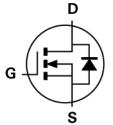
- Case: SOT223
- Case Material: Molded Plastic, "Green" Molding Compound.
   UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Matte Tin Finish (§3)
- Weight: 0.112 grams (Approximate)







Pin Out - Top



Equivalent Circuit

#### **Ordering Information** (Note 4)

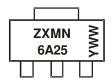
Part Number	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
ZXMN6A25GTA	ZXMN6A25	7	12	1,000

Notes:

- 1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.
- See http://www.diodes.com/quality/lead\_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

## **Marking Information**

SOT223



ZXMN6A25 = Product Type Marking Code YWW = Date Code Marking Y or  $\overline{Y}$  = Last Digit of Year (ex: 5= 2015) WW or  $\overline{W}W$  = Week Code (01~53)



#### **Maximum Ratings** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Units		
Drain-Source Voltage			V <sub>DSS</sub>	60	V
Gate-Source Voltage			V <sub>GSS</sub>	±20	V
Continuous Drain Current, $V_{GS} = 10V$ $Steady \\ State$ $T_A = +25^{\circ}C \text{ (Note 6)} \\ T_A = +70^{\circ}C \text{ (Note 6)} \\ T_A = +25^{\circ}C \text{ (Note 5)}$			I <sub>D</sub>	6.7 5.4 4.8	А
Maximum Body Diode Forward Current (Note 6)			Is	5.7	Α
Pulsed Drain Current (Note 7)			I <sub>DM</sub>	28.5	Α
Pulsed Source Current (Note 7)			I <sub>SM</sub>	28.5	Α

### Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Units	
Total Power Dissipation Linear Derating Factor	$T_A = +25^{\circ}C \text{ (Note 5)}$	P <sub>D</sub>	2 16	W mW/°C
Total Power Dissipation Linear Derating Factor	T <sub>A</sub> = +25°C (Note 6)	P <sub>D</sub>	3.9 31	W mW/°C
Thermal Resistance, Junction to Ambient	Steady state (Note 5)	D	62.5	°C/W
Thermal nesistance, building to Ambient	Steady state (Note 6)	$R_{\theta JA}$	32	°C/W
Operating and Storage Temperature Range		T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

# **Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

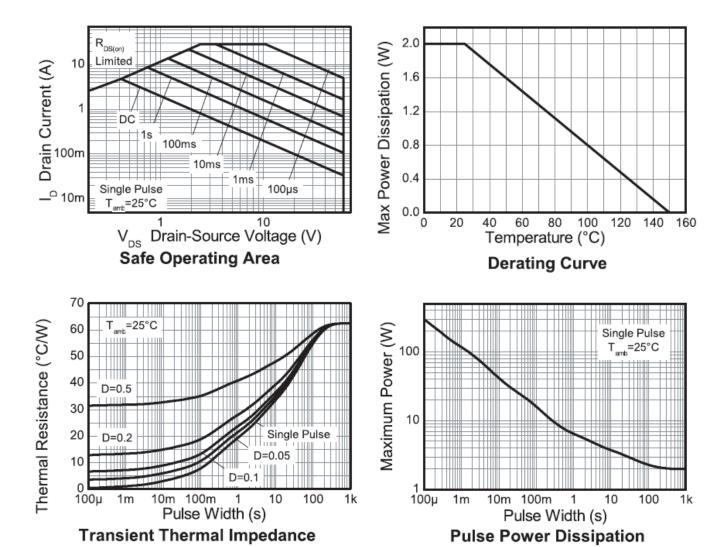
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 9)							
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	60	_	_	V	$V_{GS} = 0V, I_D = 250\mu A$	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	_	_	1.0	μΑ	$V_{DS} = 60V, V_{GS} = 0V$	
Gate-Source Leakage	I <sub>GSS</sub>	_	_	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 9)							
Gate Threshold Voltage	$V_{GS(th)}$	1.0	_	_	V	$V_{DS} = V_{GS}$ , $I_D = 250 \mu A$	
Static Drain-Source On-Resistance (Note 8)	D	_	_	50	mΩ	$V_{GS} = 10V, I_D = 3.6A$	
Static Drain-Source On-nesistance (Note 6)	R <sub>DS(ON)</sub>	_	_	70	11177	$V_{GS} = 4.5V, I_D = 3.0A$	
Diode Forward Voltage (Note 8)	$V_{SD}$	_	0.85	0.95	V	V <sub>GS</sub> = 0V, I <sub>S</sub> = 5.5A	
Forward Transconductance (Note 8 & 10)	9 <sub>fs</sub>	_	10.2	_	S	V <sub>DS</sub> = 15V, I <sub>D</sub> = 4.5A	
DYNAMIC CHARACTERISTICS (Note 10)							
Input Capacitance	Ciss	_	1,063	_		V <sub>DS</sub> = 30V, V <sub>GS</sub> = 0V f = 1.0MHz	
Output Capacitance	Coss	_	104	_	pF		
Reverse Transfer Capacitance	Crss	_	64	_			
Total Gate Charge (V <sub>GS</sub> = 5.0V)	Qg		11	_		$V_{DS} = 30V$ , $I_D = 1.4A$ ,	
Total Gate Charge (V <sub>GS</sub> = 10V)	$Q_g$		20.4	_	nC		
Gate-Source Charge	Qgs		4.1	_	i iiC		
Gate-Drain Charge	$Q_{gd}$		5.1	_			
Turn-On Delay Time	t <sub>D(on)</sub>		3.8	_		$V_{GS} = 10V, V_{DD} = 30V, R_G = 6.0\Omega,$ $I_{D} = 1.0A$	
Turn-On Rise Time	t <sub>r</sub>		4.0	_	nS		
Turn-Off Delay Time	t <sub>D(off)</sub>	_	26.2	_	113		
Turn-Off Fall Time	t <sub>f</sub>	_	10.6	_			
Body Diode Reverse Recovery Time	t <sub>rr</sub>	_	22	_	nS	L_ 2.24 dl/dt 1004/up	
Body Diode Reverse Recovery Charge	Q <sub>rr</sub>	_	21.4	_	nC	I <sub>F</sub> = 2.2A, dI/dt = 100A/µs	

Notes: 5. For a device surface mounted on 25mm x 25mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions

- 6. For a device surface mounted on FR4 PCB measured at t ≤10 secs.
  7. Repetitive rating 25mm x 25mm FR4 PCB, D = 0.02, pulse width 300µs pulse width limited by maximum junction temperature.
- 8. Measured under pulsed conditions. Width=300 $\mu$ s. Duty cycle  $\leq$  2%.
- 9. Short duration pulse test used to minimize self-heating effect.
- 10. Guaranteed by design. Not subject to product testing.

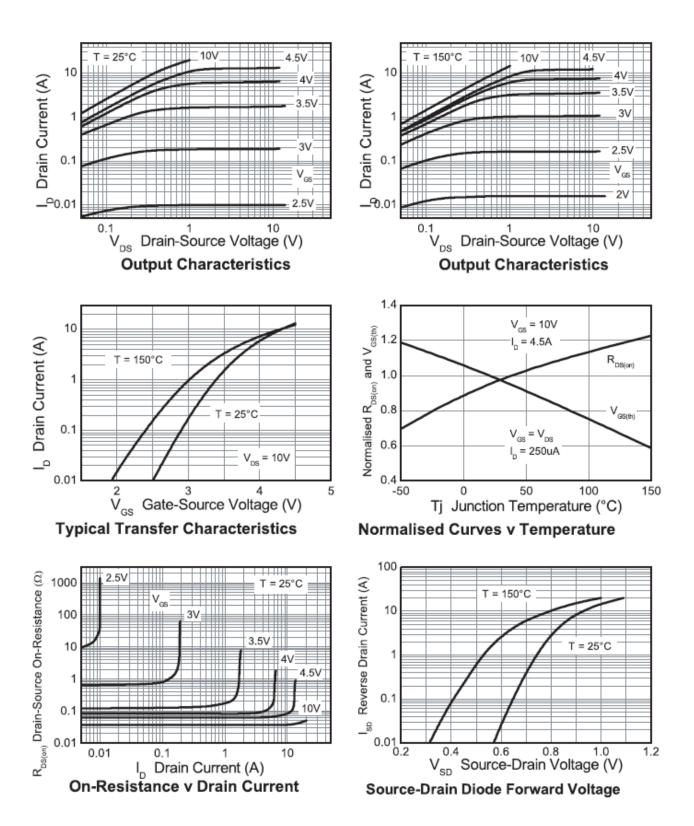


## **Typical Characteristics**



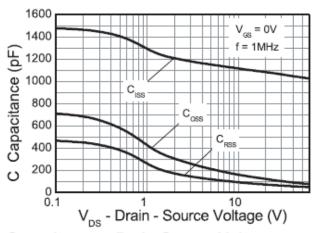


### Typical Characteristics (continued)

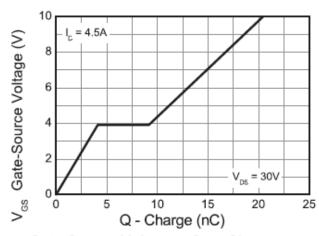




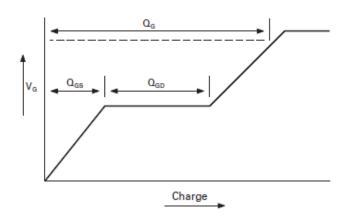
### **Typical Characteristics** (cont.)



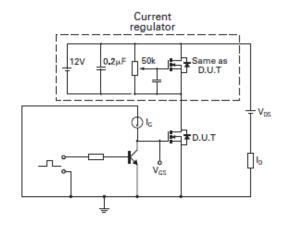
Capacitance v Drain-Source Voltage



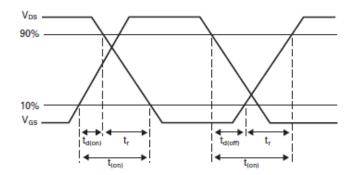
Gate-Source Voltage v Gate Charge



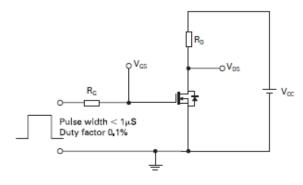
Basic gate charge waveform



Gate charge test circuit



Switching time waveforms

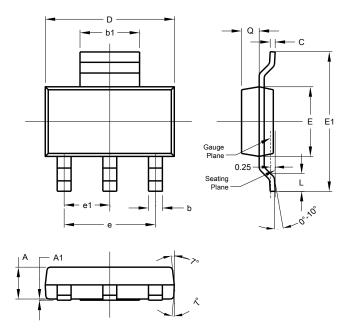


Switching time test circuit



## **Package Outline Dimensions**

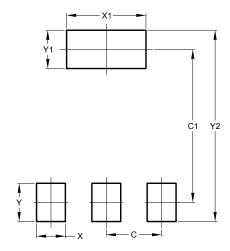
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.



SOT223					
Dim	Min	Max	Тур		
Α	1.55	1.65	1.60		
A1	0.010	0.15	0.05		
b	0.60	0.80	0.70		
b1	2.90	3.10	3.00		
С	0.20	0.30	0.25		
D	6.45	6.55	6.50		
Е	3.45	3.55	3.50		
E1	6.90	7.10	7.00		
е	<b>e</b> 4.60		4.60		
e1	-	-	2.30		
L	0.85	1.05	0.95		
Q	0.84	0.94	0.89		
All Dimensions in mm					

# Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)		
С	2.30		
C1	6.40		
Х	1.20		
X1	3.30		
Υ	1.60		
Y1	1.60		
Y2	8.00		



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